

### **ISC Silicon NPN Power Transistor**

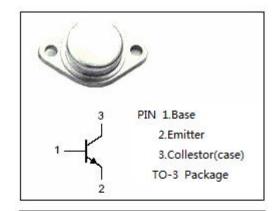
2SD1040

#### **DESCRIPTION**

- High Current Capability
- · Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

· Designed for use in switching regulators, inverters, wideband amplifiers and power oscillators in industrial and commercial applications.

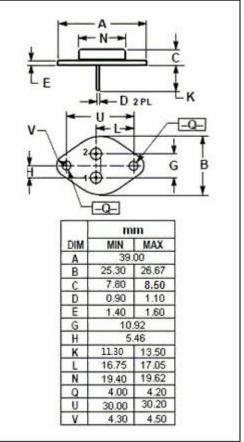


# ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector- Base Voltage	150	V
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
Ic	Collector Current-Continuous	15	Α
I <sub>B</sub>	Base Current-Continuous	5	Α
Pc	Collector Power Dissipation @T <sub>C</sub> =25℃	150	W
TJ	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	1.25	°C/W





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#### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

1j-25 C un	ness otherwise specified								
SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT				
$V_{\text{CEO}(\text{SUS})}$	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA ; I <sub>B</sub> = 0	100		V				
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 15A; I <sub>B</sub> = 1.5A		2.0	V				
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 15A; I <sub>B</sub> = 1.5A		3.0	V				
I <sub>CBO</sub>	Collector Base Cutoff Current	V <sub>CB</sub> =150V; I <sub>E</sub> = 0		0.5	mA				
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7.0V; I <sub>C</sub> = 0		1.0	mA				
h <sub>FE -1</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 4V	35	200					
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 15A ; V <sub>CE</sub> = 4V	20						
Switching times									
t <sub>r</sub>	Rise Time			1.2	μS				
t <sub>s</sub>	Storage Time	V <sub>CC</sub> = 30V, I <sub>C</sub> = 15A , I <sub>B1</sub> = -I <sub>B2</sub> = 1.5A,		3.0	μS				
t <sub>f</sub>	Fall Time			1.8	μs				

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